

Abstract Submitted  
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**Three-layer Hall model analysis of Hall measurements from Al-GaN layers** MO AHOJJJA, S. ELHAMRI, Physics, University of Dayton — Temperature dependent Hall Effect measurements were performed on Si doped AlGaN layers before and after irradiation with 1 MeV electrons. Unlike GaN samples, a reliable two-donor fit could not be obtained for any of the investigated AlGaN samples, whether they were irradiated or unirradiated. It may be that for these samples, the two layer analysis is inadequate to yield the precise bulk carrier concentration and mobility.

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